

Figure S1 SV-G/S configurations based on symmetry considerations (E_b represents the binding energy).

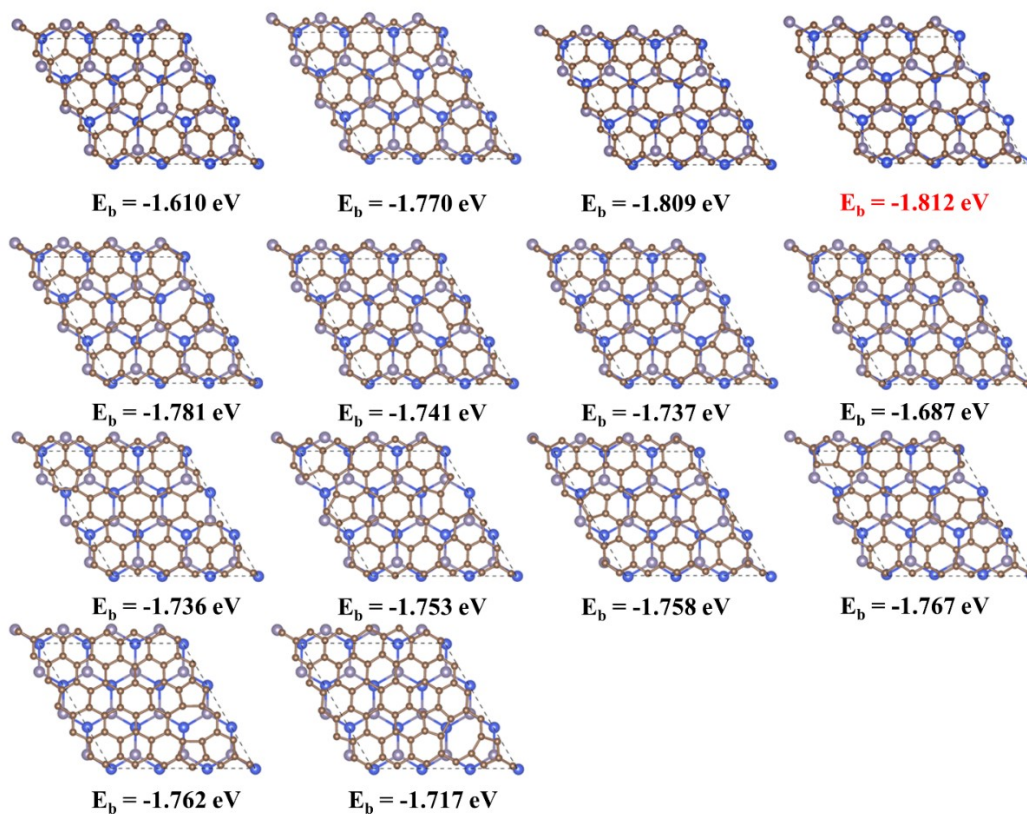


Figure S2 DV-G/S configurations based on symmetry considerations. (E_b represents the binding energy).

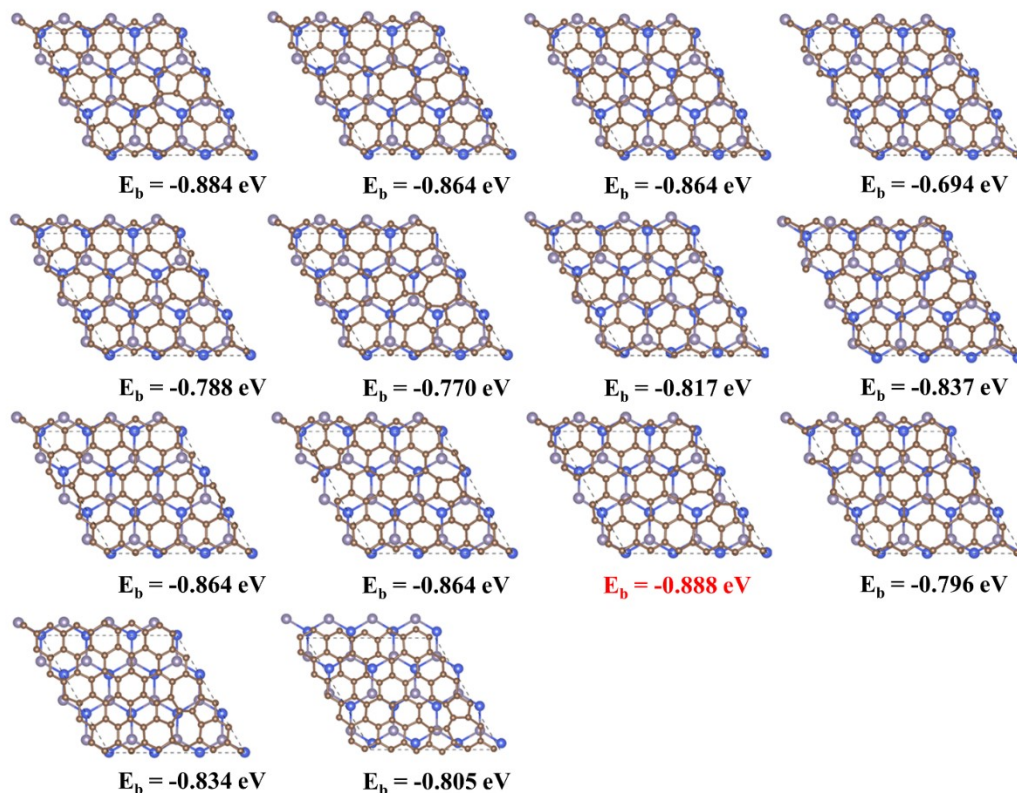


Figure S3 SW-G/S configurations based on symmetry considerations. (E_b represents the binding energy).

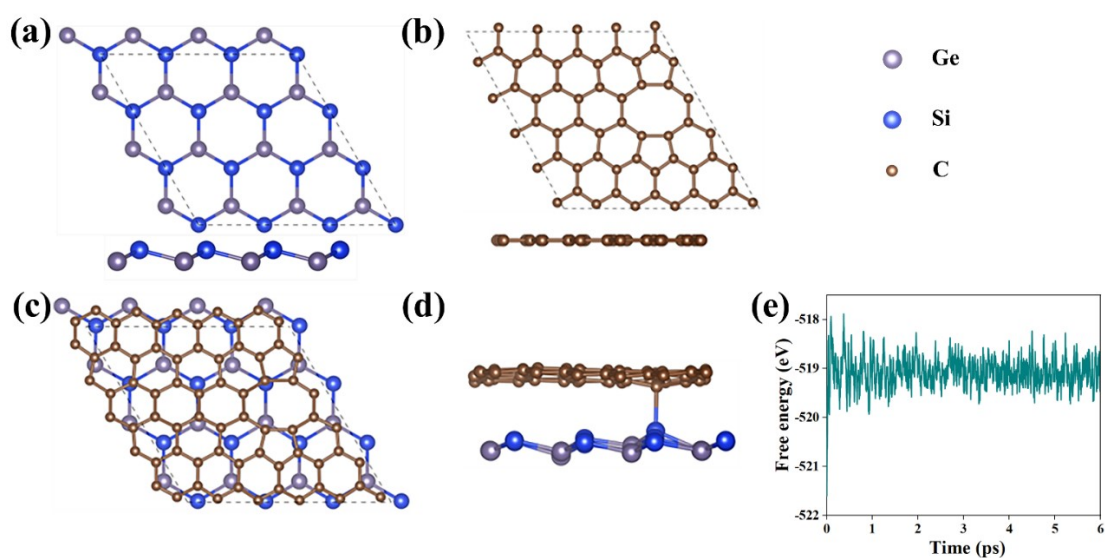


Figure S4 (a) Top and side views of the structure of 2D SiGe. (b) Top and side views of the structure of graphene with DV defect. (c) Top and (d) side view the

structure of DV-G/S. (e) Free Energy as a function of MD time at a temperature of 300K for DV-G/S.

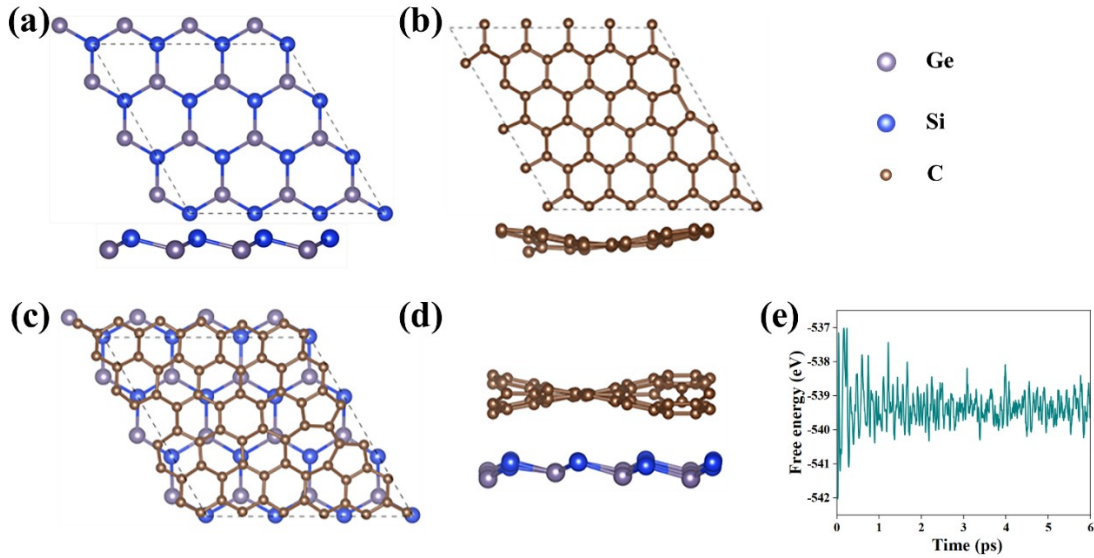


Figure S5 (a) Top and side views of the structure of 2D SiGe. (b) Top and side views of the structure of graphene with SW defect. (c) Top and (d) side view the structure of SW-G/S. (e) Free Energy as a function of MD time at a temperature of 300K for SW-G/S.

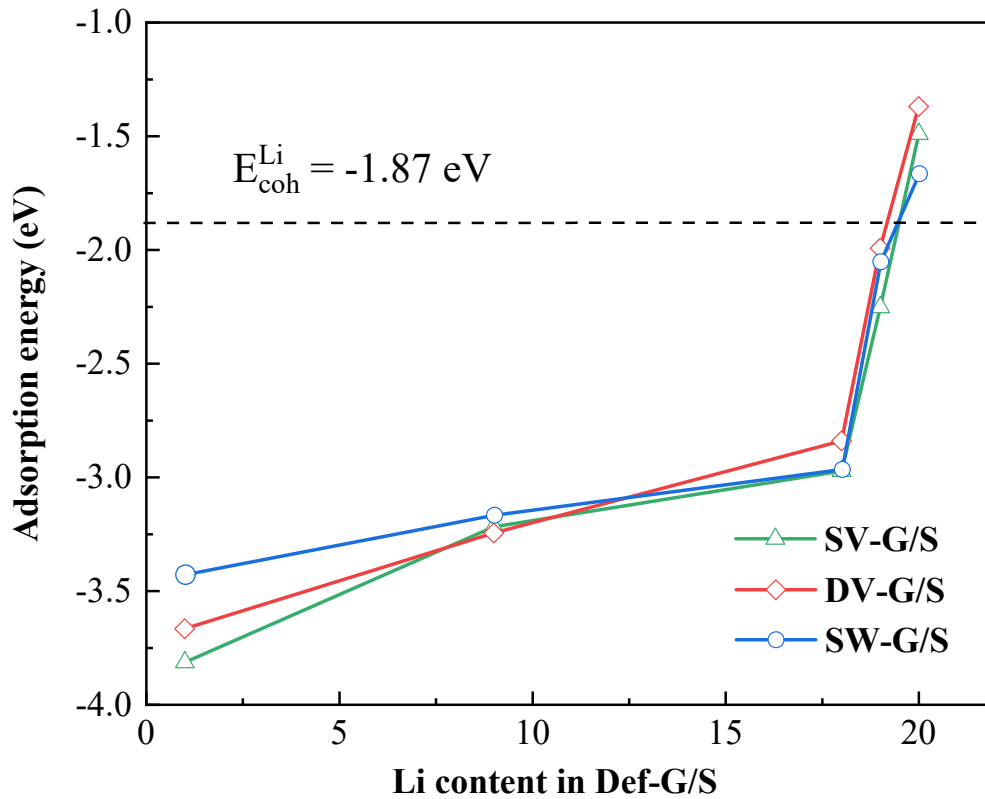


Figure S6 Li adsorption energies of SV-G/S, DV-G/S and SW-G/S as a function of Li adsorption concentration.